

# F Fuji Electric ht 6MBI150VB-060-50

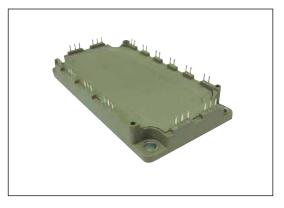
# IGBT MODULE (V series) 600V / 150A / 6 in one package

# Features

Compact Package P.C.Board Mount Low VCE (sat)

## Applications

Inverter for Motor Drive AC and DC Servo Drive Amplifier Uninterruptible Power Supply Industrial machines, such as welding machines



# Maximum Ratings and Characteristics

# ● Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

Items		Symbols	Conditions	Conditions		Units		
(	Collector-Emitter voltage		Vces				V	
0	Gate-Emitter voltage		V <sub>GES</sub>				V	
rter	Collector current		lc	Continuous	Tc=80°C	150		
۵ I			Іср	1ms	Tc=80°C	300	٨	
≦ '			-lc		· · · ·		A	
			-lc pulse	1ms	1ms			
(	Collector power dissipation		Pc	1 device	1 device		W	
Junction temperature		Tj				°C		
Operating junciton temperature (under switching conditions)			Тјор					
Case temperature		Тс						
Storage temperature		Tstg						
sol	ation voltage	between terminal and copper base (*1) between thermistor and others (*2)	Viso	AC : 1min.	AC : 1min.		VAC	
Scr	ew torque	Mounting (*3)	-	M5	M5		N m	

Note \*1: All terminals should be connected together during the test.

Note \*2: Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

Note \*3: Recommendable value : 2.5-3.5 Nm (M5)

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### • Electrical characteristics (at Tj= 25°C unless otherwise specified)

4.0.		Sympole	Sumhala Canditiana			aracteris	tics	Units
tems		Symbols	Conditions		min.	typ.	max.	
	Zero gate voltage collector current	Ices	V <sub>GE</sub> = 0V, V <sub>CE</sub> = 600V		-	-	1.0	mA
	Gate-Emitter leakage current	Iges	$V_{GE} = 0V, V_{GE} = \pm 20V$		-	-	200	nA
	Gate-Emitter threshold voltage	V <sub>GE (th)</sub>	V <sub>CE</sub> = 20V, I <sub>c</sub> = 150mA		6.2	6.7	7.2	V
	Collector-Emitter saturation voltage	V <sub>CE (sat)</sub> (terminal)	V <sub>GE</sub> = 15V I <sub>c</sub> = 100A	Tj=25°C	-	2.45	2.90	- V
				Tj=125°C	-	2.75	-	
				Tj=150°C	-	2.95	-	
		V <sub>CE (sat)</sub> (chip)	V <sub>GE</sub> = 15V Ic = 150A	Tj=25°C	-	1.60	2.05	
				Tj=125°C	-	1.90	-	
				Tj=150°C	-	2.10	-	
H	Internal gate resistance	Rg(int)	-		-	6	-	Ω
	Input capacitance	Cies	V <sub>CE</sub> = 10V, V <sub>GE</sub> = 0V, f = 1MHz		-	9.7	-	nF
	Turn-on time	ton		-	0.36	1.20	μs	
Inverter		tr	Vcc = 300V	-	0.25	0.60		
		tr (i)	│Ic = 150A │Vge = +15 / -15V	-	0.07	-		
Ì	Town off these	toff	$R_{\rm g} = 9\Omega$	-	0.52	1.20		
	Turn-off time	tf		-	0.03	0.45		
Ì	Forward on voltage	V⊧ (terminal)		Tj=25°C	-	2.45	2.90	- V
			I⊧ = 150A	Tj=125°C	-	2.35	-	
		(terminal)		Tj=150°C	-	2.30	-	
			I⊧ = 150A	Tj=25°C	-	1.60	2.05	
		V⊧ (chip)		Tj=125°C	-	1.50	-	
				Tj=150°C	-	1.45	-	1
Ì	Reverse recovery time	trr	I <sub>F</sub> = 150A		-	-	0.35	μs
5	Desistence	R	T = 25°C		-	5000	-	Ω
Thermistor	Resistance		T = 100°C		465	495	520	
1	B value	В	T = 25 / 50°C		3305	3375	3450	K

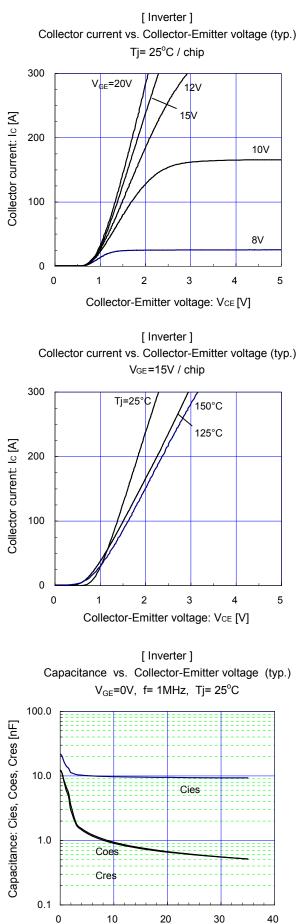
#### • Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
Items		Conditions	min.	typ.	max.	Units
"hormol reciptores (1 device)	Rth(j-c)	Inverter IGBT	-	-	0.31	°C/W
Thermal resistance (1device)		Inverter FWD	-	-	0.60	
Contact thermal resistance (1device) (*4)	Rth(c-f)	with Thermal Compound	-	0.05	-	

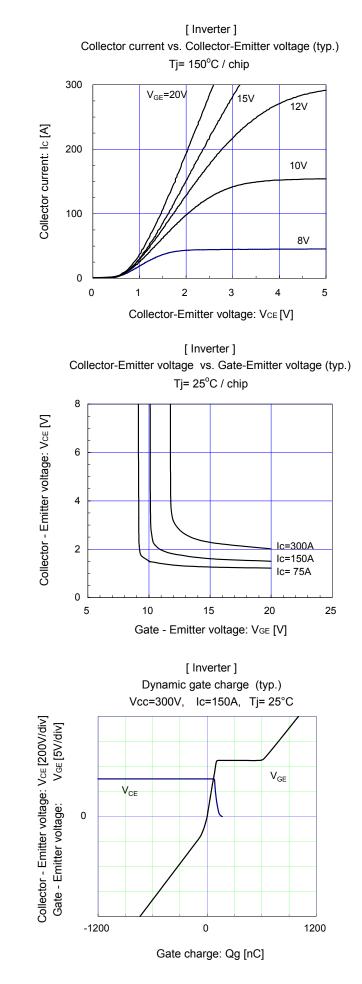
Note \*4: This is the value which is defined mounting on the additional cooling fin with thermal compound.

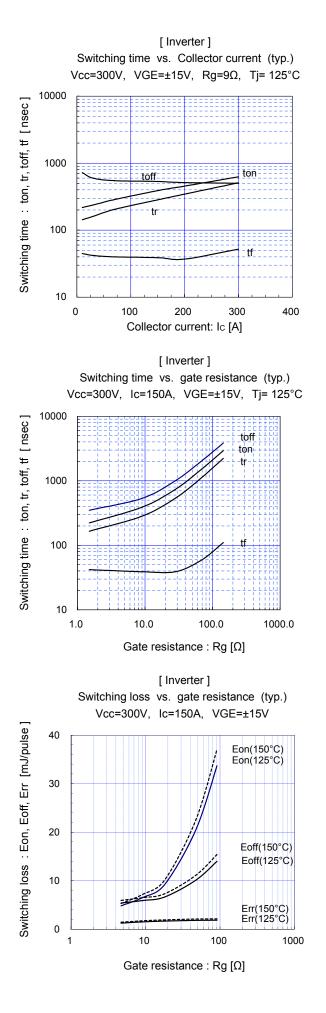
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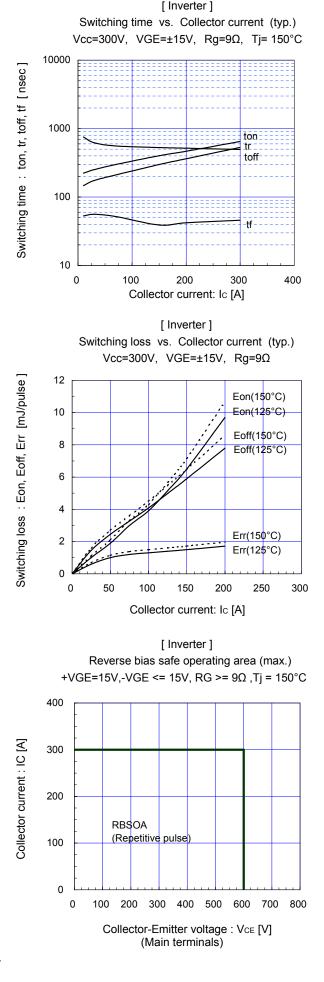
#### Characteristics (Representative)

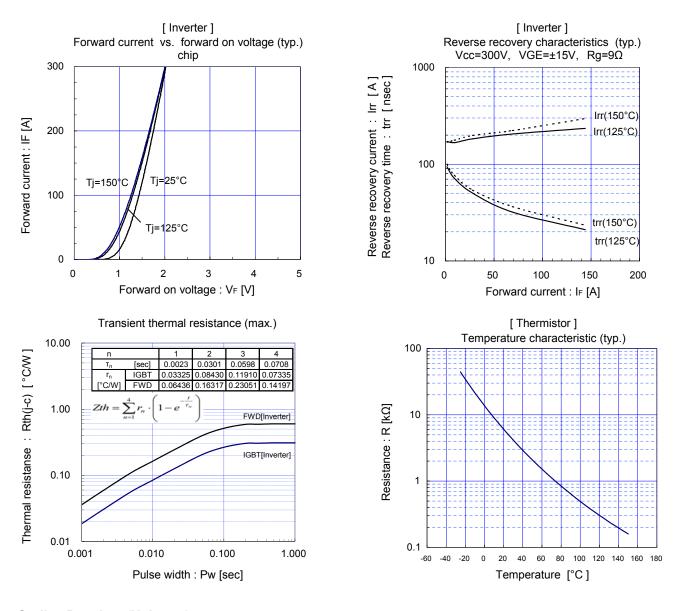


Collector - Emitter voltage: VCE [V]

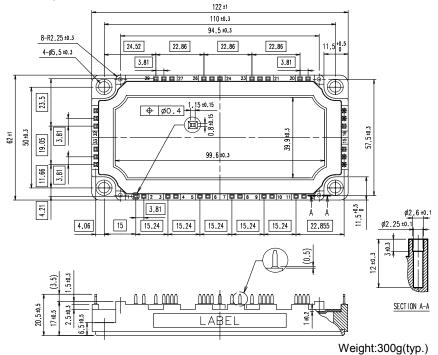












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### Equivalent Circuit

